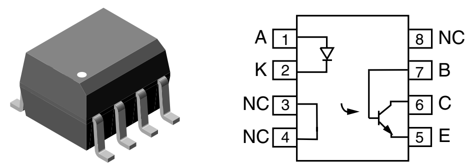
Optocoupler, Phototransistor Output, With Base Connection in SOIC-8 package

Features

- High BV_{CEO}, 70 V
- Isolation Test Voltage, 3000 V_{RMS}
- Industry Standard SOIC-8A Surface Mountable Package
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



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Agency Approvals

- UL1577, File No. E52744 System Code Y
- DIN EN 60747-5-2 (VDE0884)
  DIN EN 60747-5-5 pending
  Available with Option 1

Description

The IL205AT/ IL206AT/ IL207AT/ IL208AT are optically coupled pairs with a Gallium Arsenide infrared LED and a silicon NPN phototransistor. Signal information, including a DC level, can be transmitted by the device while maintaining a high degree of electrical isolation between input and output. This family comes in a standard SOIC-8A small outline package for surface mounting which makes them ideally suited for high density application with limited space. In addition to eliminating through-hole requirements, this package conforms to standards for surface mounted devices.

A specified minimum and maximum CTR allows a narrow tolerance in the electrical design of the adjacent circuits. The high BV_{CEO} of 70 V gives a higher safety margin compared to the industry standard 30 V.

Order Information

Part	Remarks
IL205AT	CTR 40 - 80 %, SOIC-8
IL206AT	CTR 63 - 125 %, SOIC-8
IL207AT	CTR 100 - 200 %, SOIC-8
IL208AT	CTR 160 - 320 %, SOIC-8

Available on Tape and Reel only.

For additional information on the available options refer to Option Information.

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

Input

Parameter	Test condition	Symbol	Value	Unit
Peak reverse voltage		V_R	6.0	V
Forward continuous current		I_F	60	mA
Power dissipation		P_{diss}	90	mW
Derate linearly from 25 °C			1.2	mW/°C

Output

Parameter	Test condition	Symbol	Value	Unit
Collector-emitter breakdown voltage		BV_{CEO}	70	V
Emitter-collector breakdown voltage		BV_{ECO}	7.0	V
Collector-base breakdown voltage		BV_{CBO}	70	V
$I_{CMAX\ DC}$		$I_{CMAX\ DC}$	50	mA
I_{CMAX}	t < 1.0 ms	I_{CMAX}	100	mA
Power dissipation		P_{diss}	150	mW
Derate linearly from 25 °C			2.0	mW/°C

Coupler

Parameter	Test condition	Symbol	Value	Unit
Total package dissipation (LED + detector)		P_{tot}	240	mW
Derate linearly from 25 °C			3.3	mW/°C
Operating temperature		T_{amb}	- 55 to + 100	°C
Storage temperature		T_{stg}	- 55 to + 150	°C
Soldering time	at 260 °C		10	s

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified
Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

Input

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	I_F = 10 mA	V_F		1.3	1.5	V
Reverse current	V_R = 6.0 V	I_R		0.1	100	μA
Capacitance	V_R = 0 V	C_O		13		pF

Output

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector-emitter breakdown voltage	I_C = 100 μA	BV_{CEO}	70			V
Emitter-collector breakdown voltage	I_E = 100 μA	BV_{ECO}	7.0	10		V
Collector-emitter leakage current	V_{CE} = 10 V	I_{CEO}		5.0	50	nA

Coupler

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Saturation voltage, collector-emitter	I_C = 2.0 mA, I_F = 10 mA	V_{CEsat}			0.4	V
Isolation test voltage		V_{ISO}	3000			V_{RMS}
Equivalent DC, isolation voltage			3535			VDC
Capacitance (input-output)		C_{IO}		0.5		pF
Resistance, input to output		R_{IO}		100		Ω

Current Transfer Ratio

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Current Transfer Ratio	I_F = 10 mA, V_{CE} = 5.0 V	IL205AT	CTR	40		80	%
		IL206AT	CTR	63		125	%
		IL207AT	CTR	100		200	%
		IL208AT	CTR	100		320	%
	I_F = 1.0 mA, V_{CE} = 5.0 V	IL205AT	CTR	13	25		%
		IL206AT	CTR	22	40		%
		IL207AT	CTR	34	60		%
		IL208AT	CTR	56	95		%

Switching Characteristics

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Switching time	I_C = 2 mA, R_L = 100 Ω, V_{CC} = 10 V	t_{on}, t_{off}		3.0		μs

Typical Characteristics (Tamb = 25 °C unless otherwise specified)

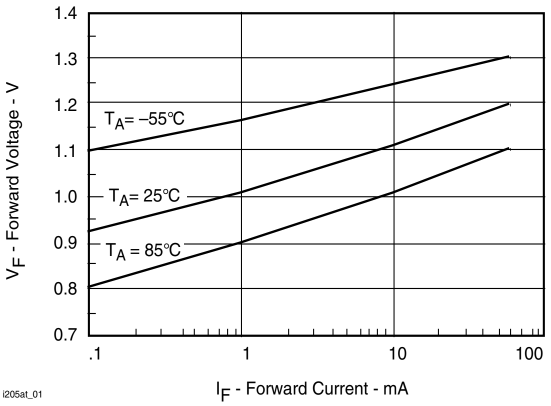

Figure 1. Forward Voltage vs. Forward Current

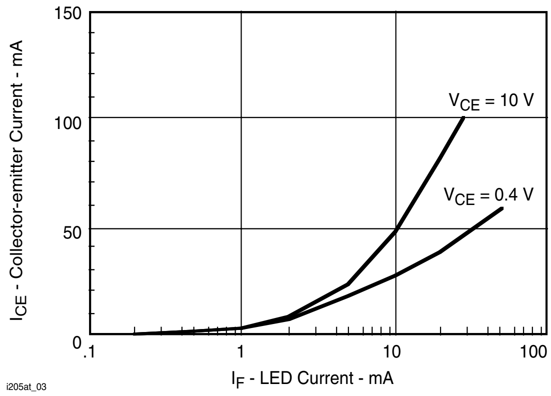

Figure 3. Collector-Emitter Current vs.LED Current

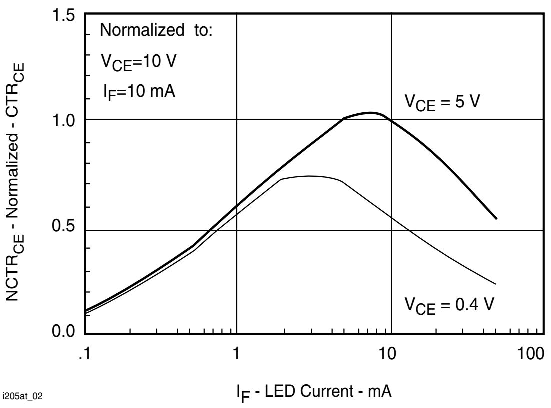

Figure 2. Normalized Non-saturated and Saturated CTR_{CE} vs. LED Current

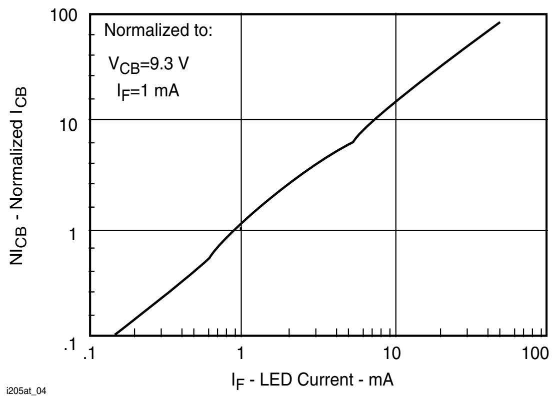

Figure 4. Normalized Collector-Base Photocurrent vs. LED Current

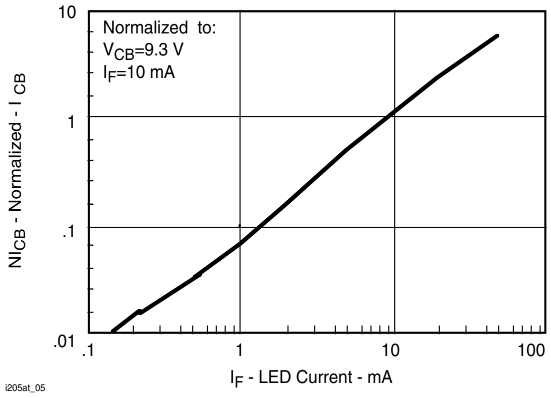

Figure 5. Normalized Collector-Base Photocurrent vs. LED Current

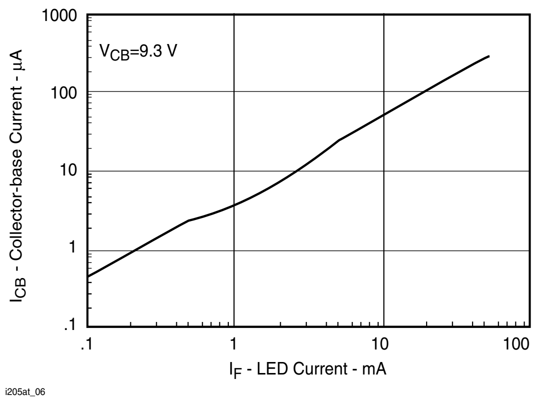

Figure 6. Collector-Emitter Photocurrent vs. LED Current

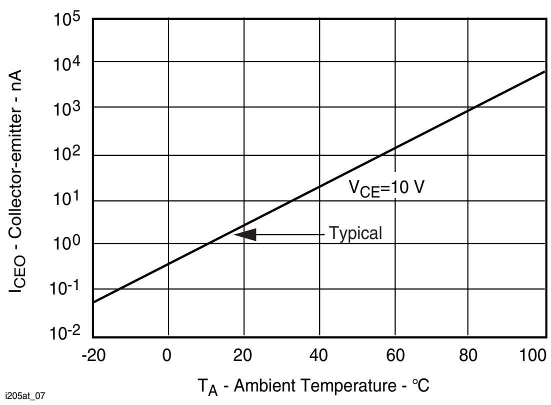

Figure 7. Collector-Emitter Photocurrent vs. LED Current

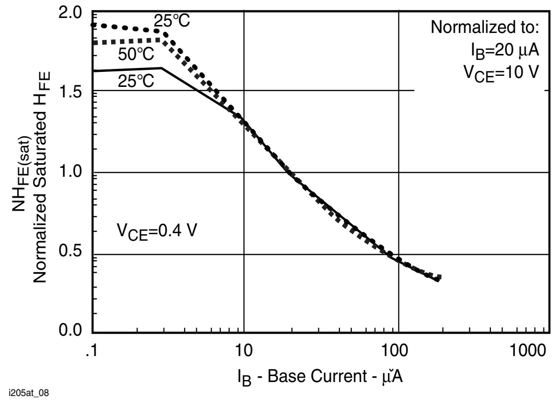

Figure 8. Base Current vs. I_F and HFE

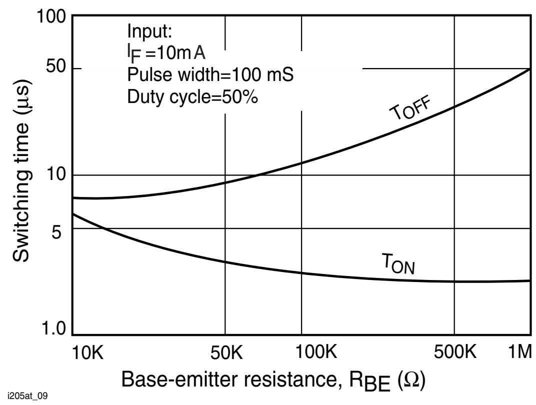

Figure 9. Typical Switching Characteristics vs. Base Resistance (Saturated Operation)

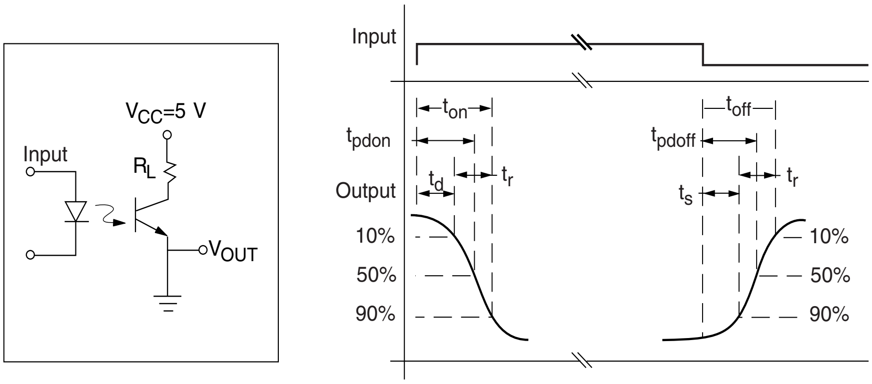

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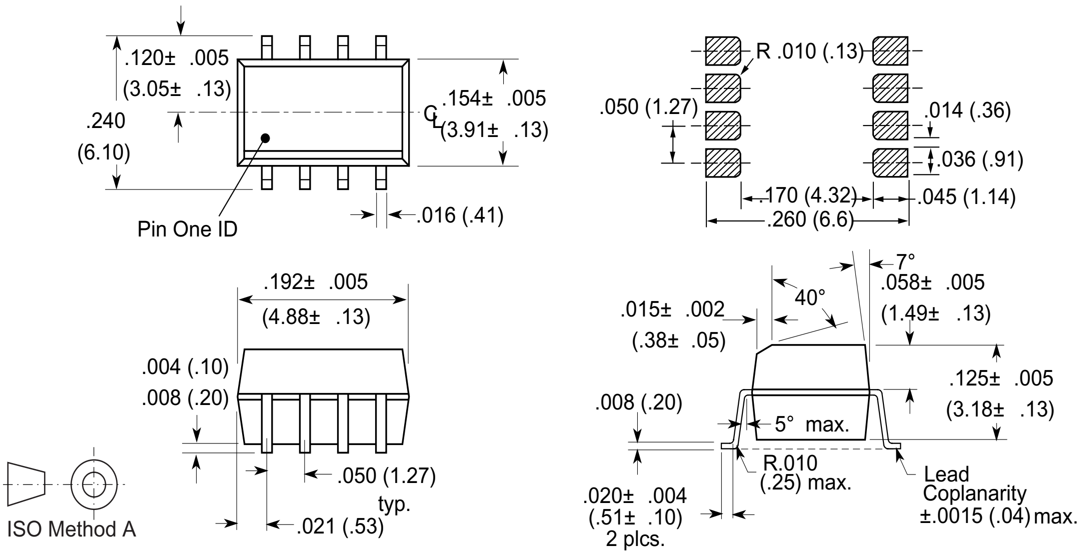
Figure 10. Switching Test Circuit

Package Dimensions in Inches (mm)



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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